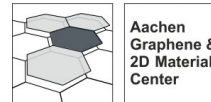


2D Materials for Energy Harvesting Applications and the Scaling-up Route

Max C. Lemme

AMO GmbH, Aachen

RWTH Aachen University – Chair of Electronic Devices



2D Materials for Energy Harvesting

RWTH Aachen University

- Large European Technical Univ.
- 50.000 students
- Triangle:
 - Germany / Belgium / Netherlands
- Chair of Electronic Devices

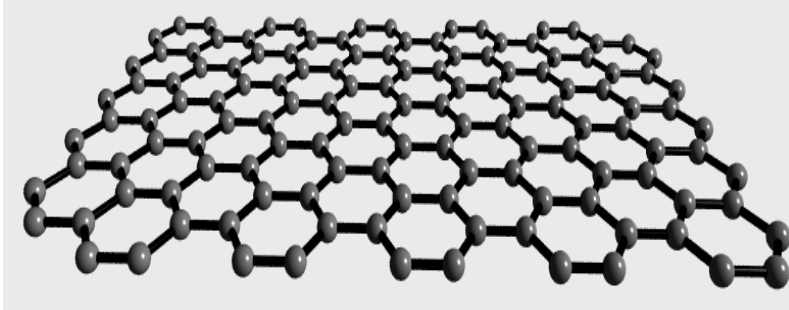


AMO GmbH

- High-Tech SME / Institute (non-profit) / Research Foundry
- 400 m² clean room
- 80 staff members in 35 funded R&D projects
- > 100 R&D partners across Europe and beyond
- Silicon technology, Nanofabrication & New Materials
- Targeted applications
 - Nanoelectronics, Sensors, Flexible Electronics
 - Nanophotonics
 - Quantum Technologies
 - Neuromorphic Computing
 - Environmental Nanotechnology
- Mission: Technology Transfer
 - R&D Partners & Start Ups (Black Semiconductor, Protemics, AMOtronic)

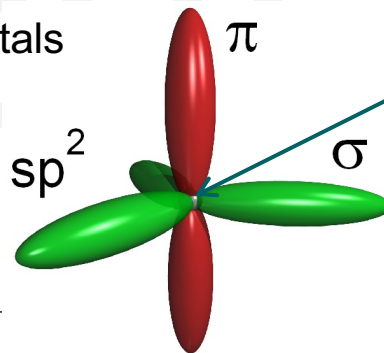
2D Materials for Energy Harvesting

Graphene: Crystal Properties

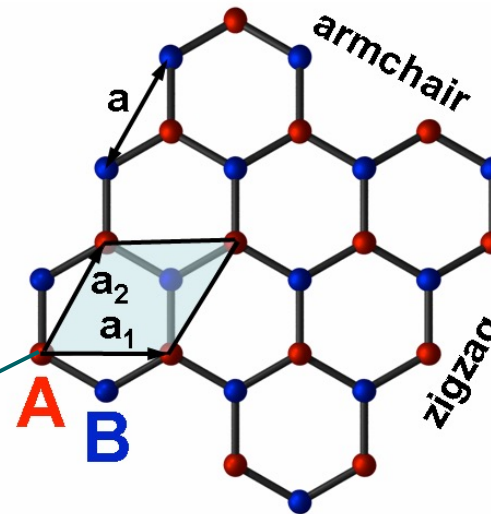


- sp^2 bonded carbon atoms ($\sim 4,3\text{eV}$)
- Graphite: stacked layers of graphene
- interlayer bond: v.d. Waals

Orbitals



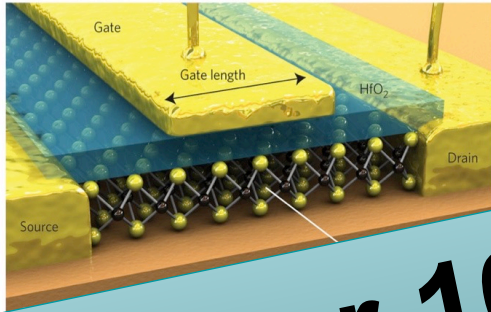
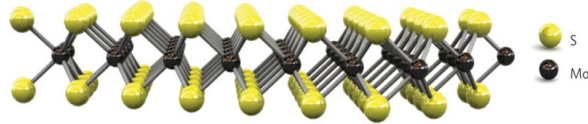
2D-crystal lattice



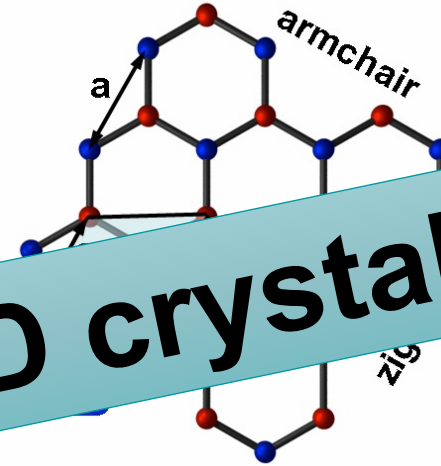
- Lattice constant: $a = 0.246\text{ nm}$
- “Thickness”: $d = 0.34\text{ nm}$

2D Materials for Energy Harvesting

Semiconductors



Insulators



...over 1000 2D crystals!

Molybdenum disulfide (MoS_2)
Transition Metal Dichalcogenides (TMDs)

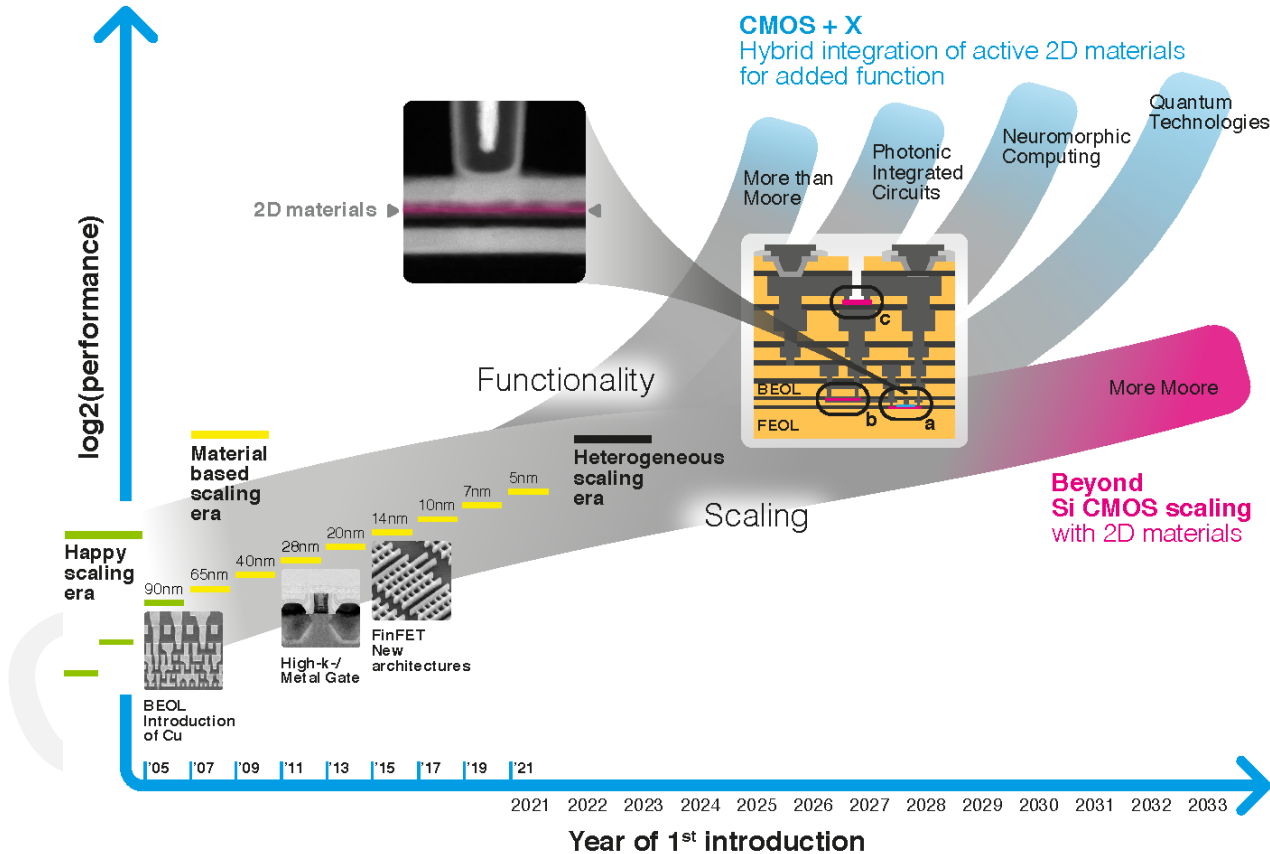
- $E_g = 1.8 \text{ eV}$
- $\mu_{\text{MoS}_2} \approx 100 \text{ cm}^2/\text{Vs}$

Radisavljevic, Nat. Nanotech. 2011.

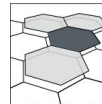
Hexagonal Boron Nitride (h-BN)

- $E_g = 5.9 \text{ eV}$
- **A** = Boron
- **B** = Nitrogen

2D Materials for Energy Harvesting

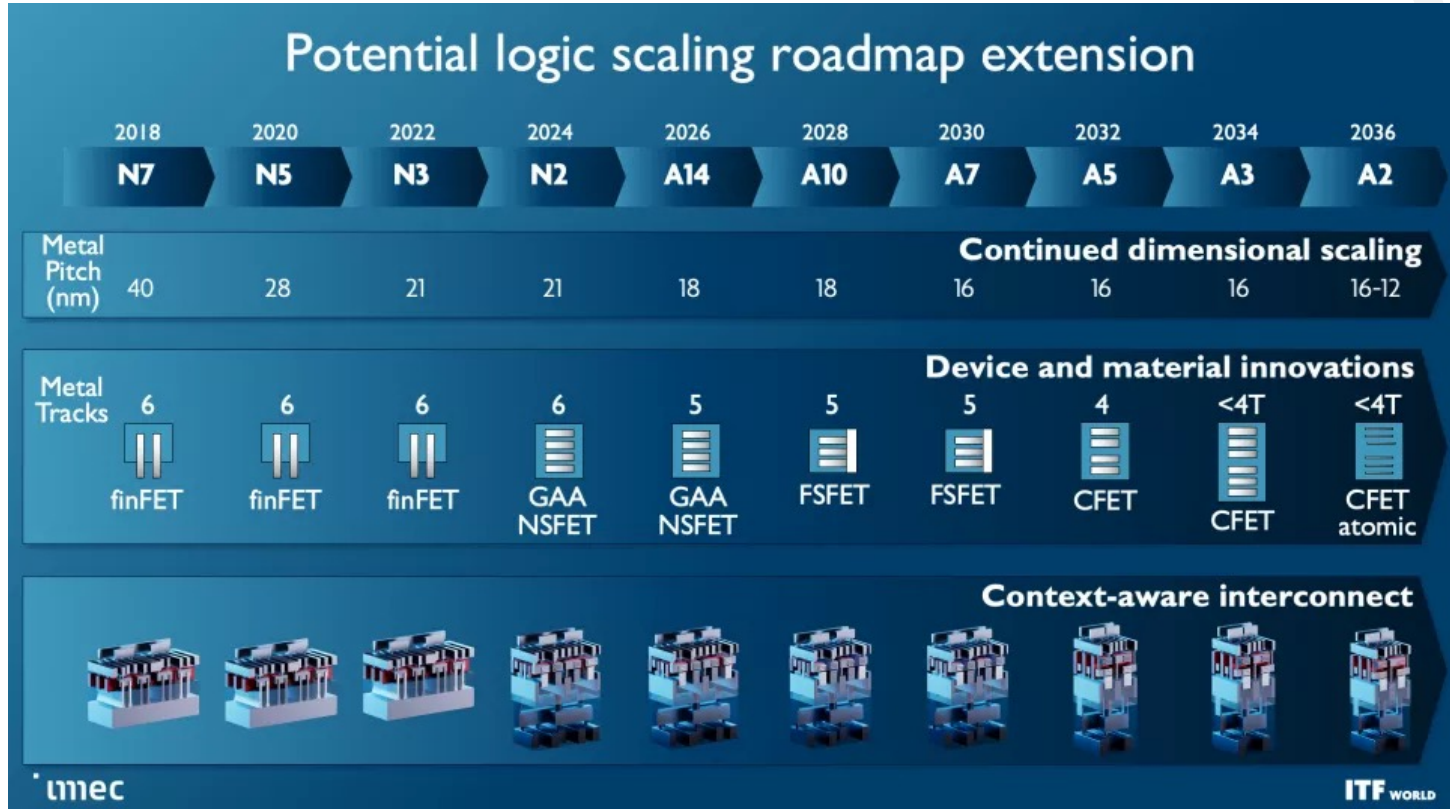


Lemme *et al.*, Nat. Comm., 2022

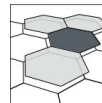


2D Materials for Energy Harvesting

imec 20-Year Semiconductor Roadmap



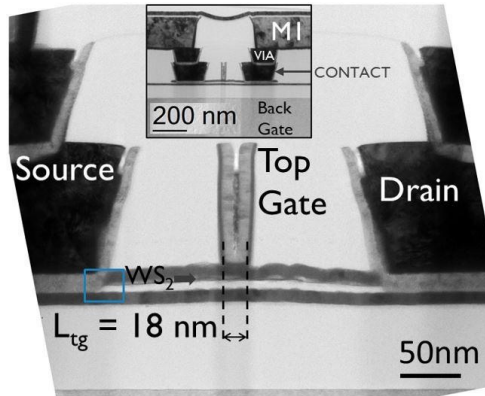
Source: <https://www.imec-int.com/en/articles/20-year-roadmap-tearing-down-walls>, 2 Aug 2022



2D Materials for Energy Harvesting

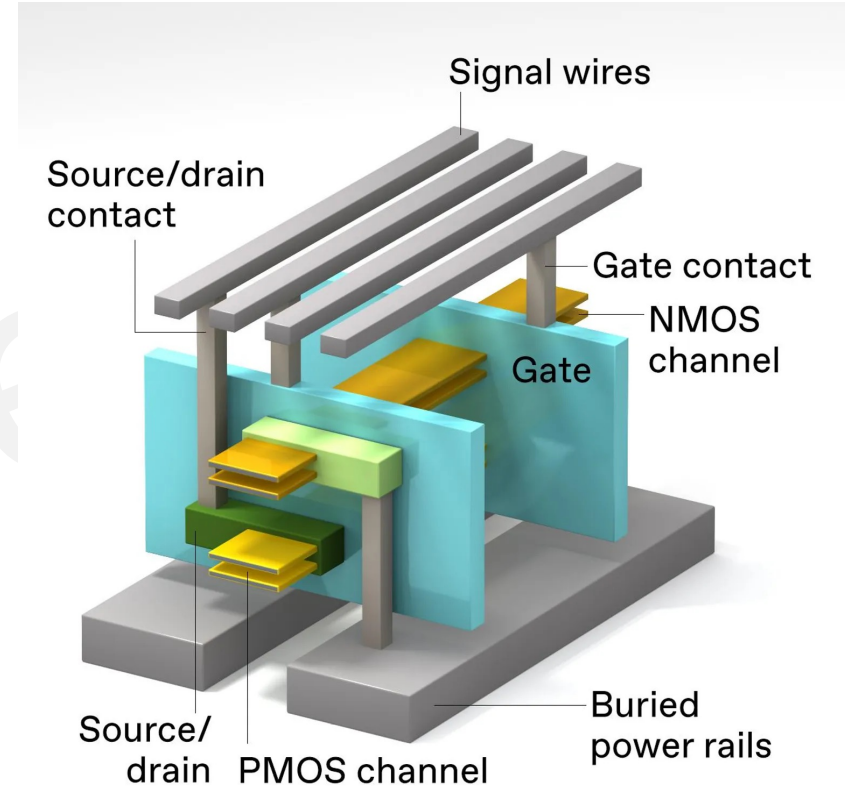
More Moore

- 2D Nanosheet FETs
 - Ultimate electrostatic control
 - No loss of mobility
 - BEOL integration → 3D



Source: IMEC

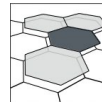
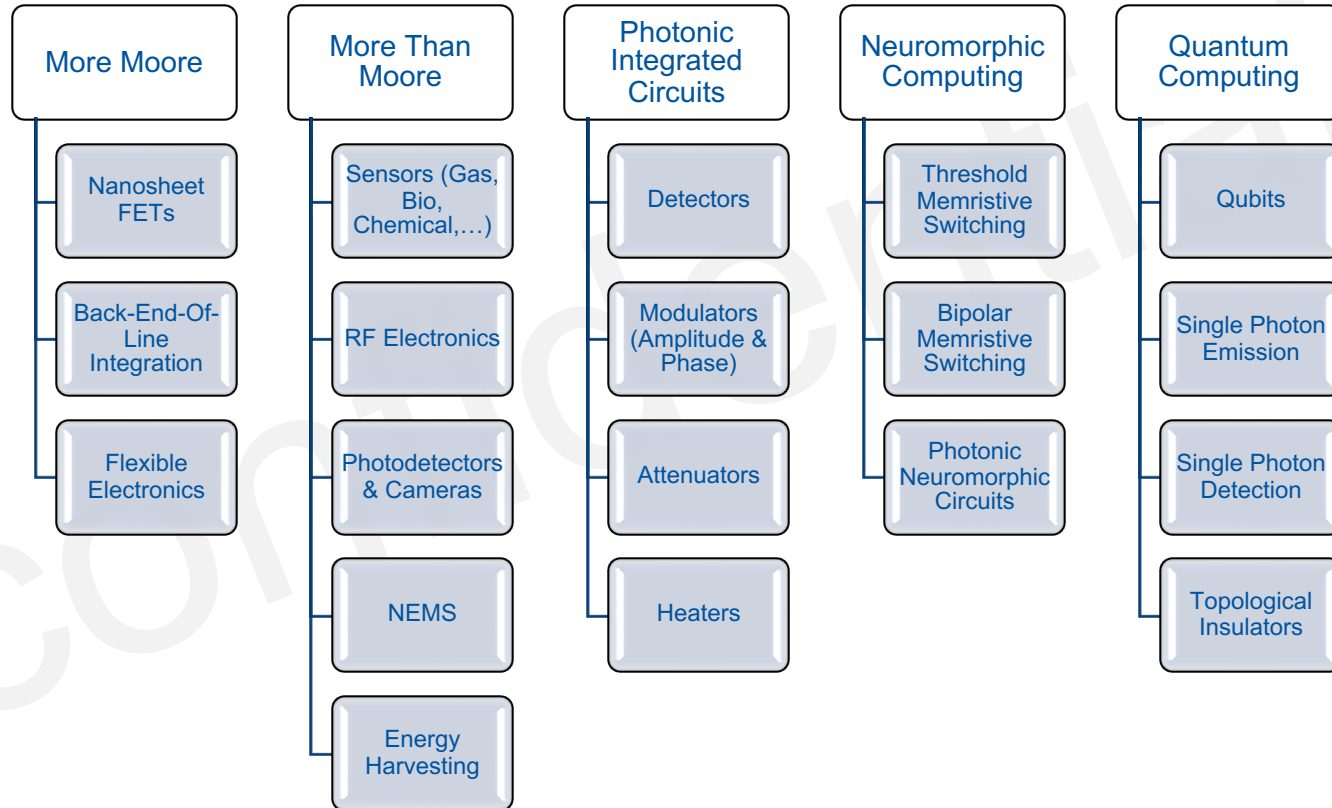
<https://www.imec-int.com/en/articles/imec-introduces-2d-materials-logic-device-scaling-roadmap>



Radosavlevic et al., IEEE Spectrum, 2022

2D Materials for Energy Harvesting

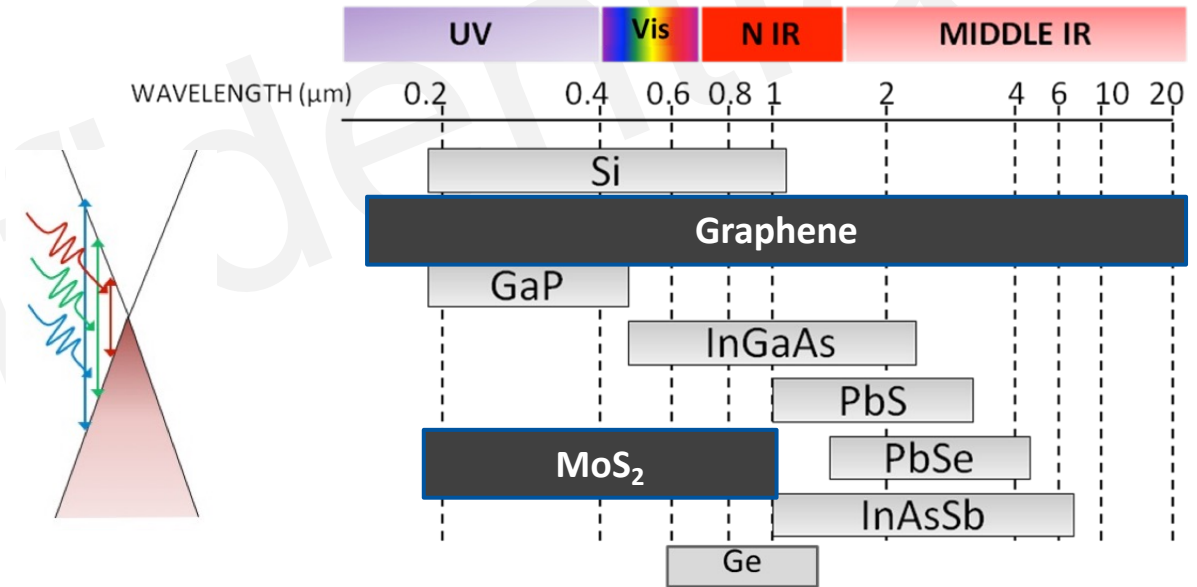
2D-Integration: Opportunities



2D Materials for Energy Harvesting

Graphene and 2D materials:

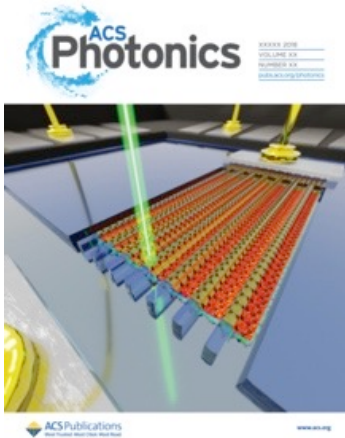
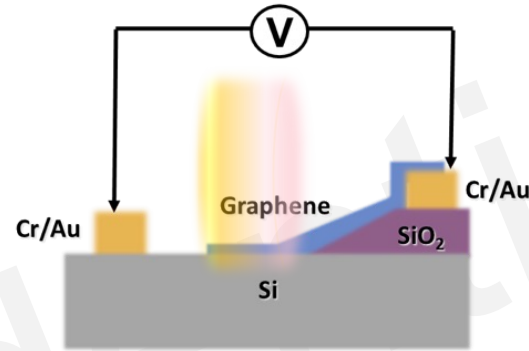
- + Ultra broad band spectral response (graphene, PtSe₂)
- + Large scale production (CVD)
- + High conductivity
- + mechanical Flexibility
- + Integrability
- ± Gate tunability
- Low absolute absorption



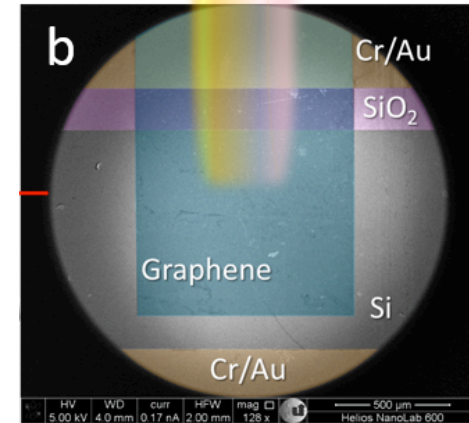
2D Materials for Energy Harvesting

Graphene /silicon Schottky diodes

- Vertical Schottky diode architecture
- High responsivity
- Ease of Integration
- Potential for infrared detection
- Potential for flexible substrates



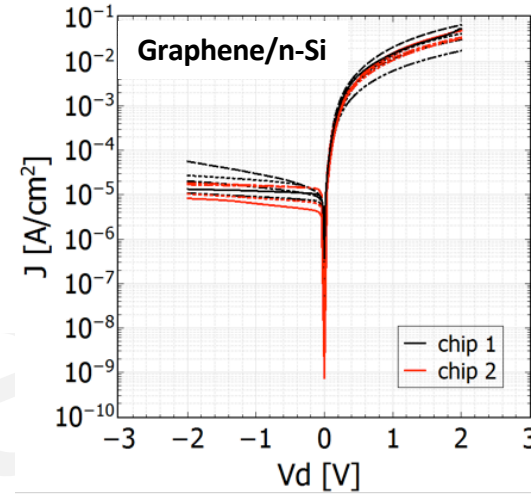
Riazimehr *et al.*, SSE, 2016
Riazimehr *et al.*, ACS Photonics, 2017
Riazimehr *et al.*, ACS Photonics, 2019



2D Materials for Energy Harvesting

Graphene / silicon Schottky diodes

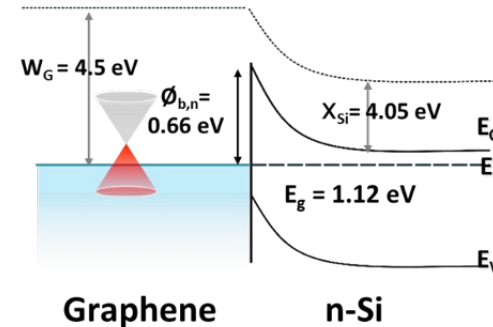
- Vertical device architecture
- High responsivity
- Ease of Integration
- Potential for infrared detection
- Potential for flexible substrates



- Shockley equation:

$$I = I_S \left[\exp\left(\frac{qV_d}{nk_B T}\right) - 1 \right]$$

- Ideality factor $n = 1.52$
- Barrier height $\phi_b = 0.66$ eV
- p doping due to exposure to ambient atmosphere

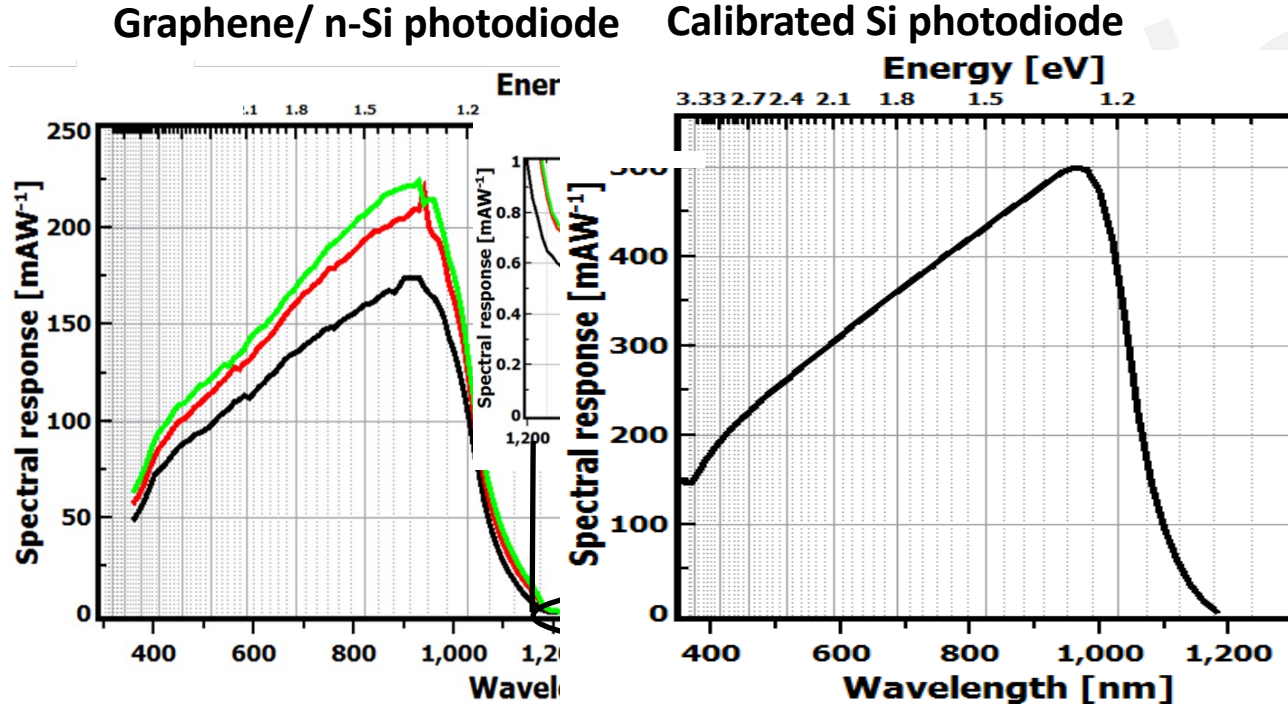


Riazimehr *et al.*, Solid State Electronics, 2016

2D Materials for Energy Harvesting

Graphene / silicon Schottky diodes: spectral response

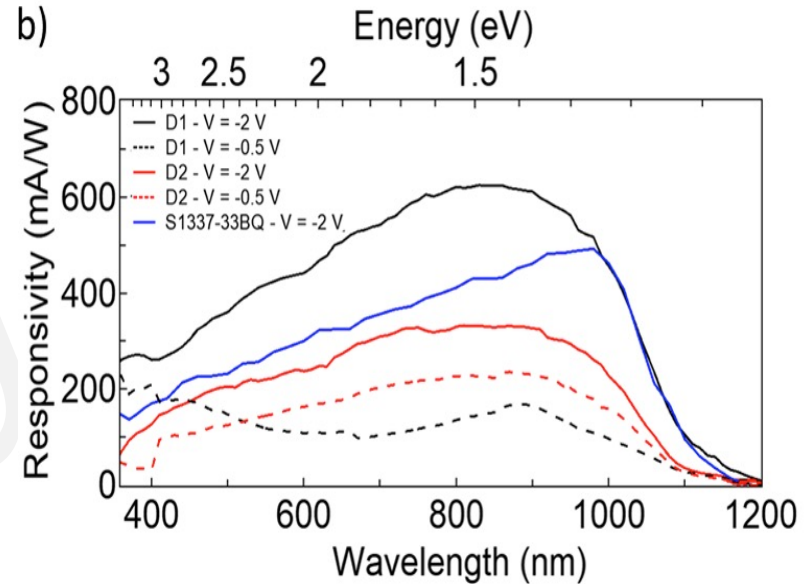
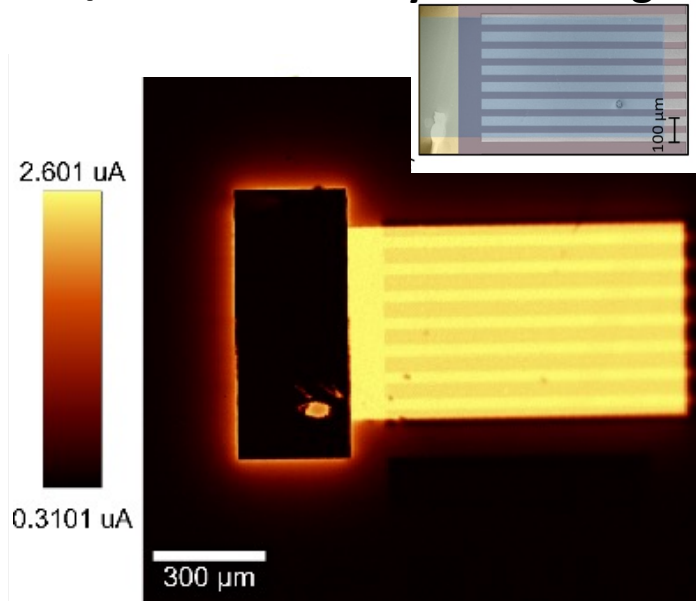
Riazimehr *et al.*, Solid State Electronics, 2016



IR : 2.3 % absorption in graphene

2D Materials for Energy Harvesting

Graphene / silicon Schottky diodes: high spectral response

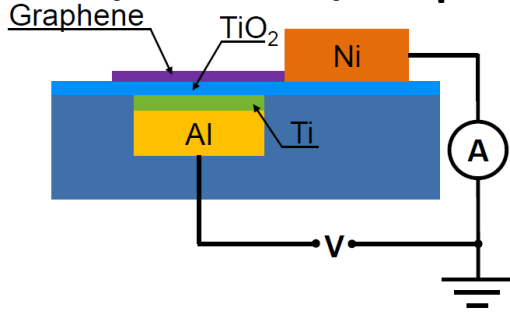


Riazimehr *et al.*, ACS Photonics, 2019

- Interdigitated diode layout
- Very high spectral response / maximum responsivity (635 mA/W) → 1.5x pure Si
- Very high quantum efficiency (>80%)
- Enabled by inversion channel under MOS structure

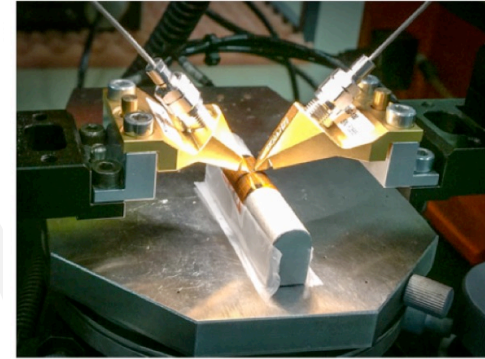
2D Materials for Energy Harvesting

Metal / Insulator / Graphene (MIG) diodes

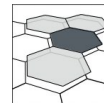
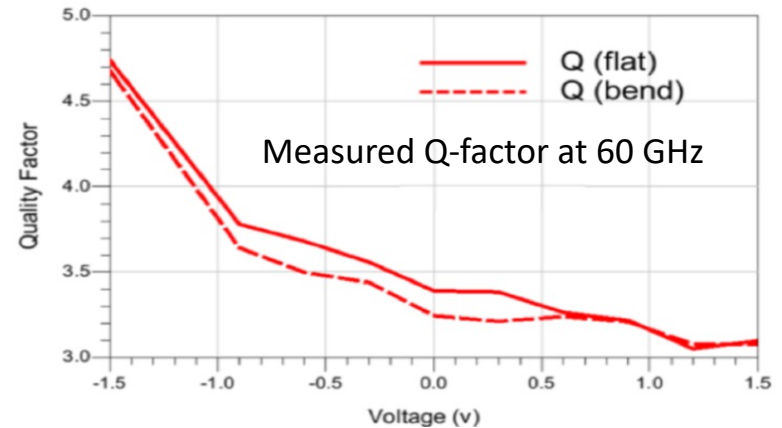
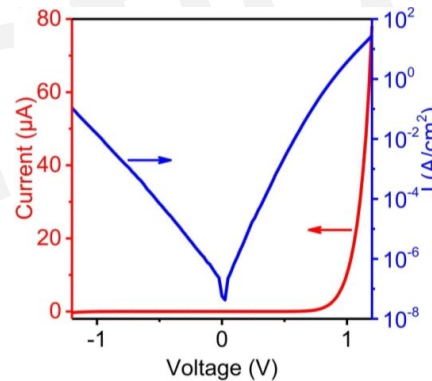
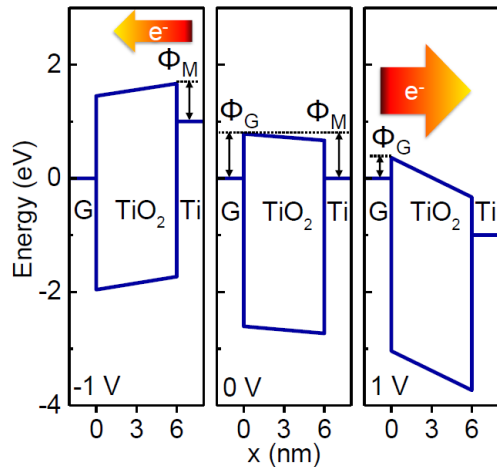


Shaygan *et al.* *Nanoscale*, 2017
 Wang *et al.*, *ACS Appl. El. Materials*, 2019
 Wang *et al.*, *Adv. El. Mat*, 2021

RF measurements of flexible diodes

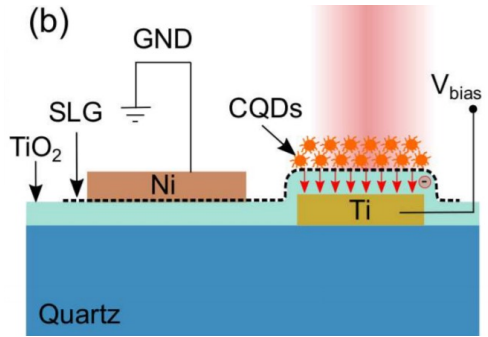


Bias induced barrier lowering

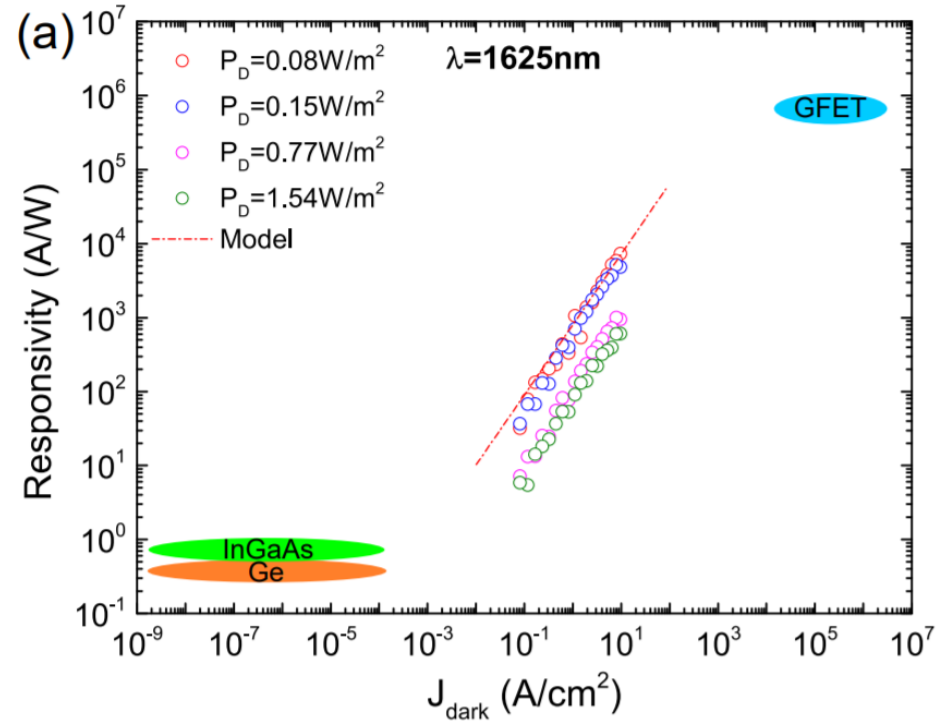
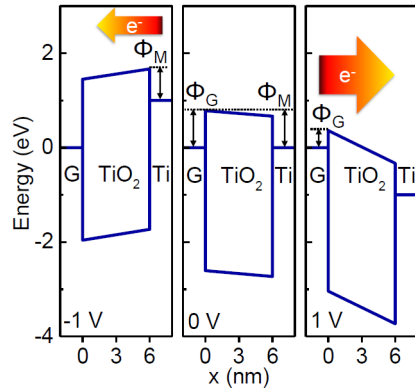


2D Materials for Energy Harvesting

Graphene / Quantum Dot Integration for IR Photodetection



Bias dependent barrier

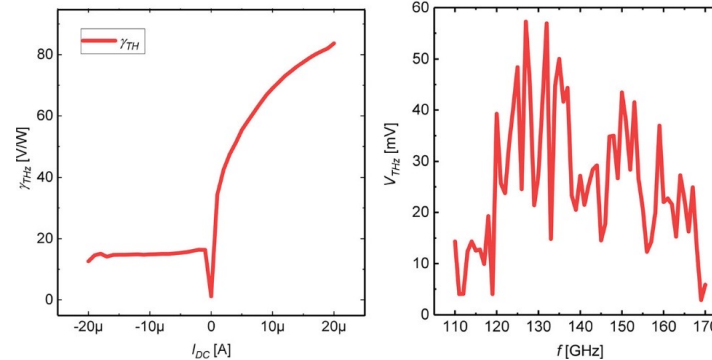
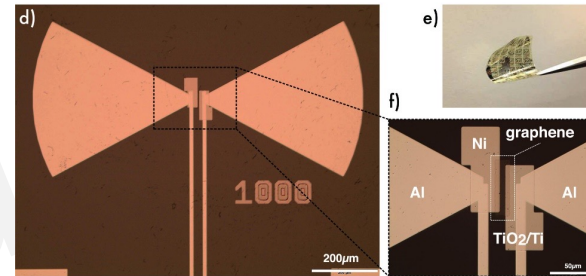
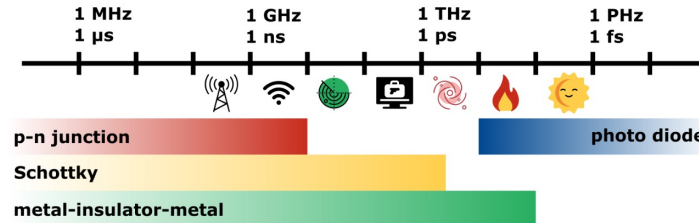


De Fazio *et al.* ACS Nano 2020

2D Materials for Energy Harvesting

Rectennas

- High RF-to-DC conversion efficiency demonstrated with monochromatic MHz-GHz sources (>90% at 2.45 GHz)
- Bottleneck in adapting to higher frequencies: response time of the rectifier
- Metal-insulator-metal diodes
 - Fast response time due to majority charge carrier transport
 - Usually low responsivity, low rectification efficiency
- Metal-insulator-graphene diodes
 - Enhanced responsivity
 - Reduced junction capacitance increases frequency response



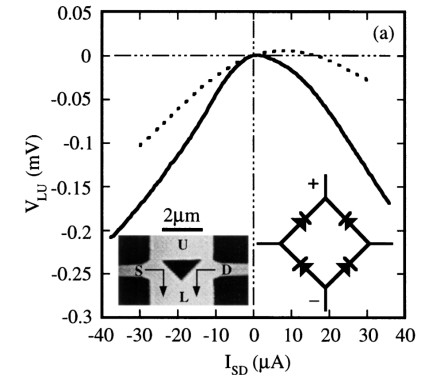
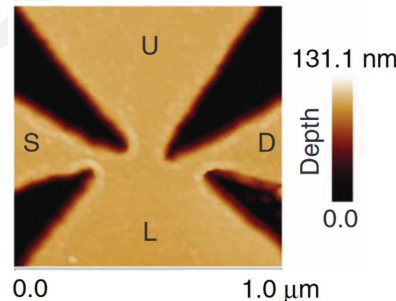
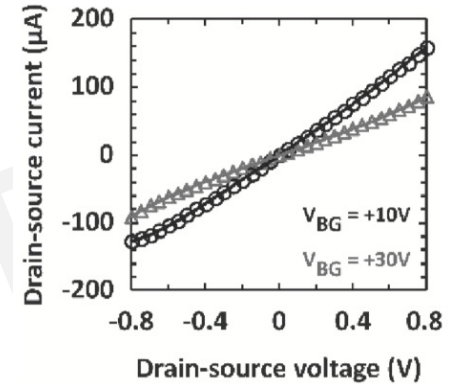
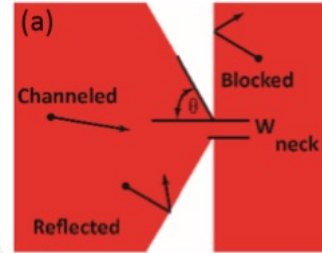
Sinohara, *River Publishers* 2017

Hemmetter *et al.*, *ACS Applied Electronic Materials* 2021

2D Materials for Energy Harvesting

Ballistic Rectification

- Ballistic rectifier
 - Charge carrier scattering occurs primarily at the device edges
 - No potential barrier inhibits current → zero-bias operation
- Two-terminal and four-terminal devices have been demonstrated
 - GaAs-AlGaAs and InAs/AlGaSb heterostructures
 - Si nanowires
 - graphene
- Long mean free path requires high charge carrier mobility



Passi et al., 2017 Silicon Nanoelectronics Workshop, 2017

Song et al., Phys. Rev. Lett. 1998

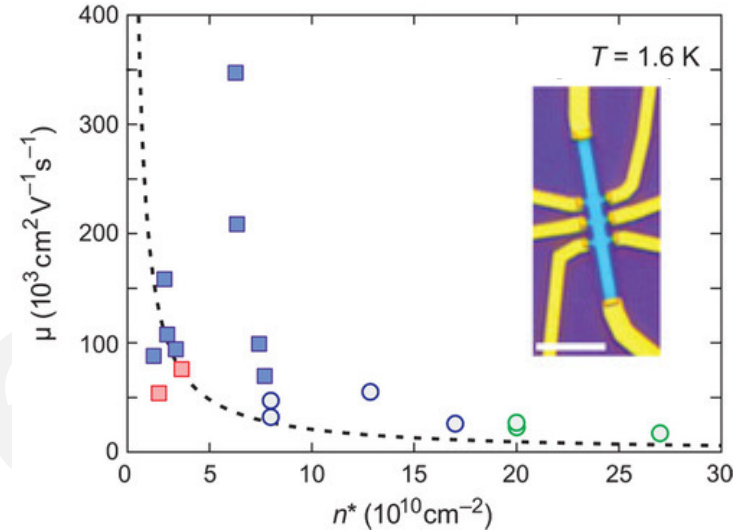
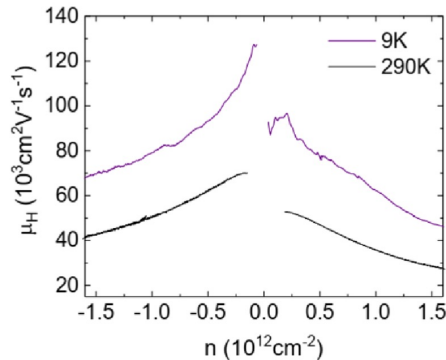
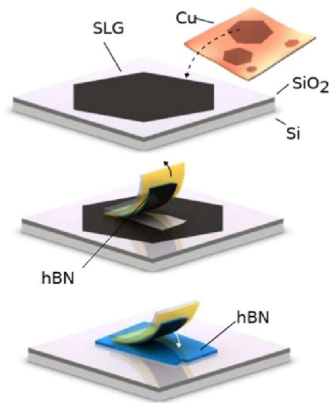
White et al., ACS Applied Nano Materials 2023

Auton et al., Nat Communications 2016

2D Materials for Energy Harvesting

Ballistic Transport in Graphene

- Graphene: mobility up to 350,000 cm²/Vs
 - On insulating substrates
 - At room temperature
 - With scalable material growth techniques (CVD)
- Mean free path > 28μm in CVD graphene
- Ballistic reflection especially important at the graphene edge



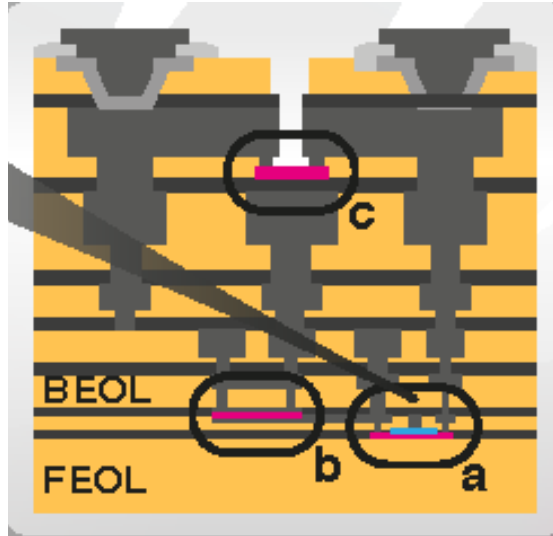
Banszerus *et al.*, *Nano Letters* 2016

Banszerus *et al.*, *Sci. Adv.* 2015

De Fazio *et al.*, *ACS Nano*, 2019

2D Materials for Energy Harvesting

2D-CMOS Integration: Challenges



Neumaier, Pindl, Lemme, Nature Materials, 2019
Akinwande *et al.*, Nature, 2019
Illarionov *et al.*, Nature Communications, 2020
Quellmaltz *et al.*, Nature Communications, 2021
Lemme *et al.*, Nature Communications, 2022

Growth

- Catalytic CVD on metals
- Temperatures: 400-1000°C
- Quality

Transfer process

- Quality
- Automation

Etching

- Etch stop → ALE

Encapsulation

- ALD vs. 2D

Electrical contacts

- ✓ Graphene
- Semiconducting 2D

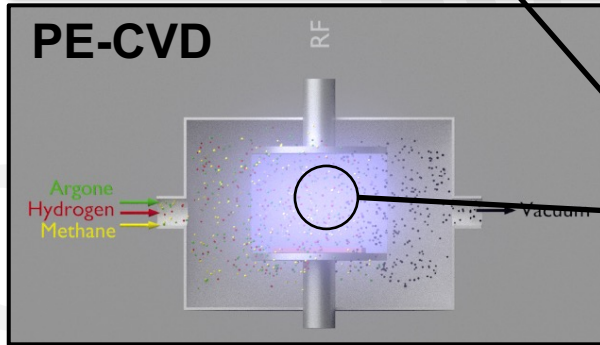
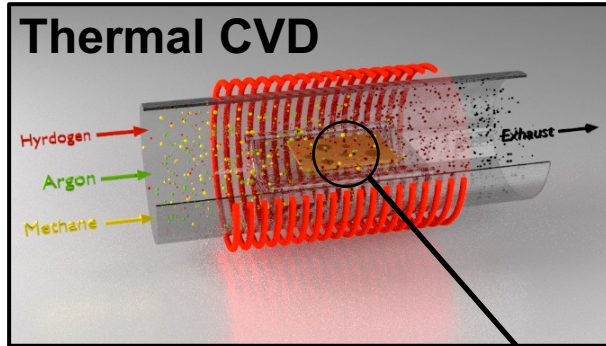
A number of **Engineering Challenges** remain before we see 2D Materials-based electronics / optoelectronics



Addressed by the **2D-Experimental Pilot Line**

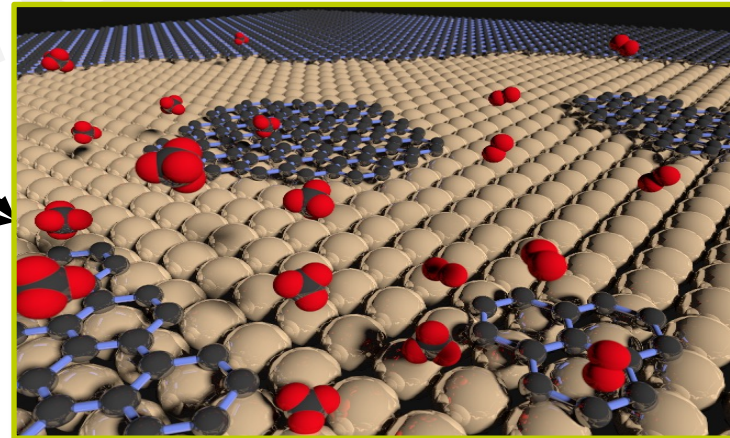
2D Materials for Energy Harvesting

Chemical vapor deposition (CVD)



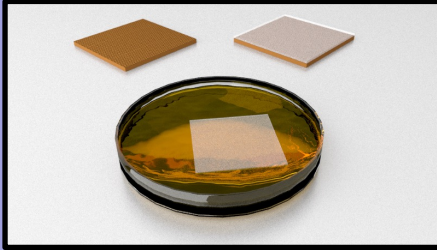
- Catalytic growth on Ni, Cu, Ru, Ir, TiC, Ta...
- + Process Temperatures: 850-1000°C
- + **Transfer to random substrates**
- **Transfer process**
- + **High potential for large areas (R2R)**
- Monolayer vs. multilayer control (solubility)
- Quality (grain boundaries, defects etc.)

S. Kataria et al., *physica status solidi (a)*, 2014., 2014



2D Materials for Energy Harvesting

Etching method



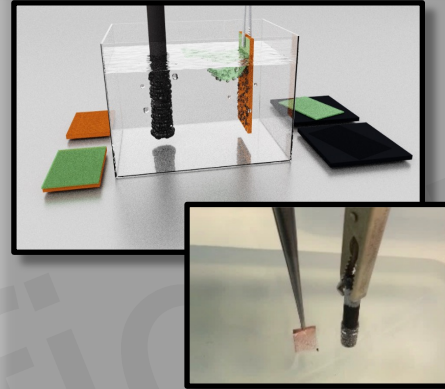
Chemical process

Copper is etched away

Etchant: FeCl_3 , Sodiumpersulfate

Duration: 1h 30min

Bubble method



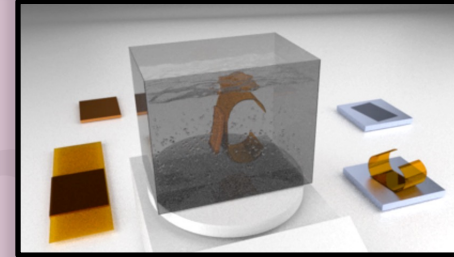
Electrochemical process

Copper is removed by bubbles created at the interface

Electrolyte: NaOH

Duration: 30s

Capillary method



Physical process (Capillary effect)

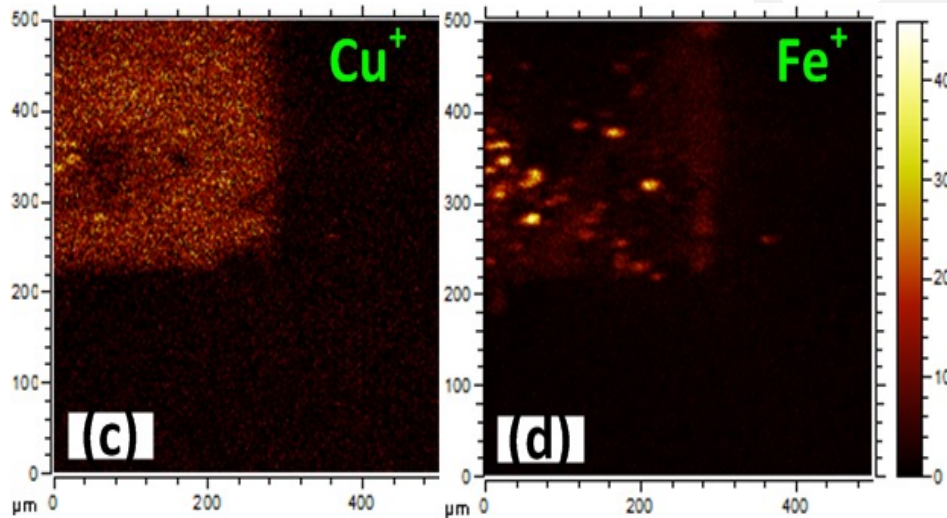
Copper is removed by water between copper and graphene

Reactant: DI-Water

Duration: 8h

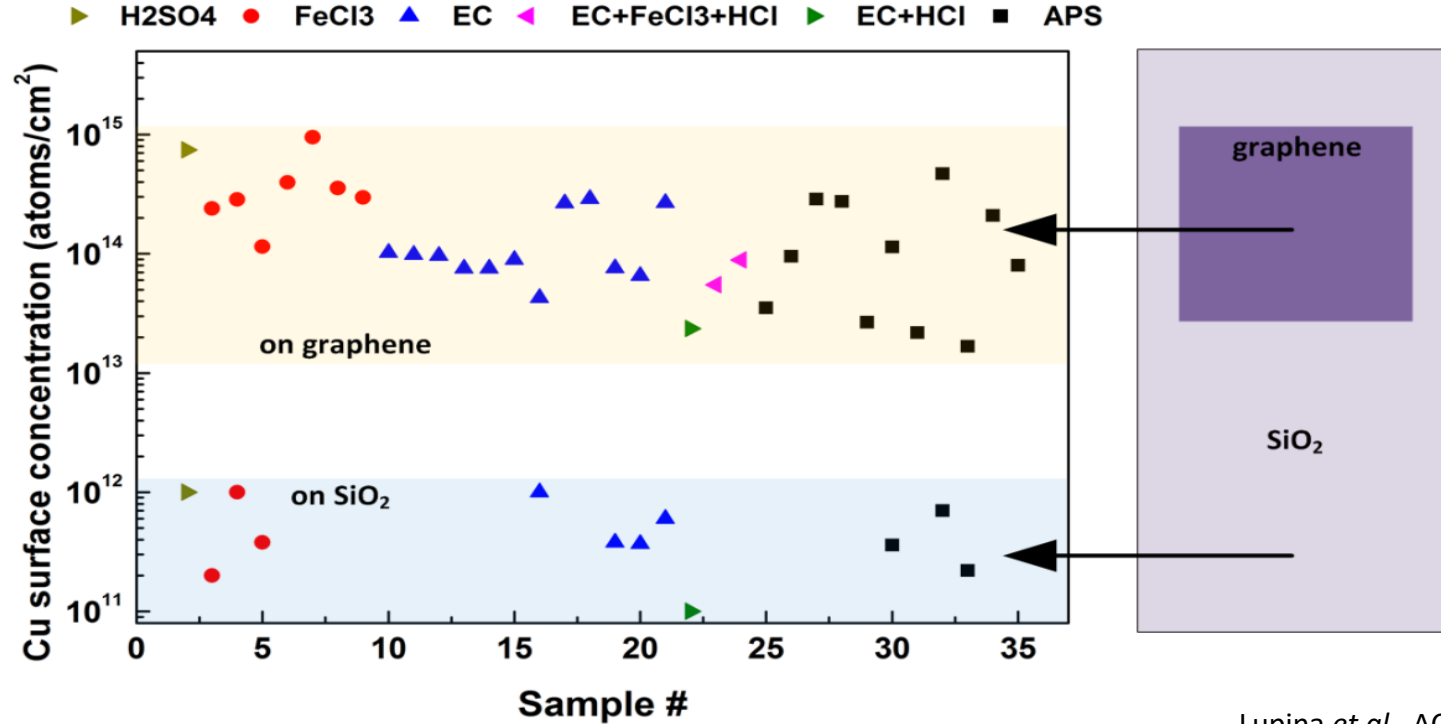
Integration challenge: contamination

- Time-of-flight secondary ion mass spectrometry (ToF-SIMS) and
- Total reflection x-ray fluorescence (TXRF) →
 - Elemental fingerprints of residual contamination with a sensitivity better than 10^9 atoms/cm².



ToF SIMS ⁶³Cu⁺ and ⁵⁶Fe⁺ maps on the corner of a graphene layer on SiO₂

Lupina *et al.*, ACS Nano, 2015



Lupina *et al.*, ACS Nano, 2015

2D Materials for Energy Harvesting

European 2D Experimental Pilot Line



- H2020 project to develop technology (not a specific application)
- Start in 10/2020, 4 years, 20 M€ funding
- Goal: technology transfer to Europractice and European Industry

1. Development of tools & materials



2. Development of module & platform



3. Multi-purpose wafer runs



Industrial Advisory Board

X-FAB

AMS

NXP

Infineon

STMicroelectronics

Emberion

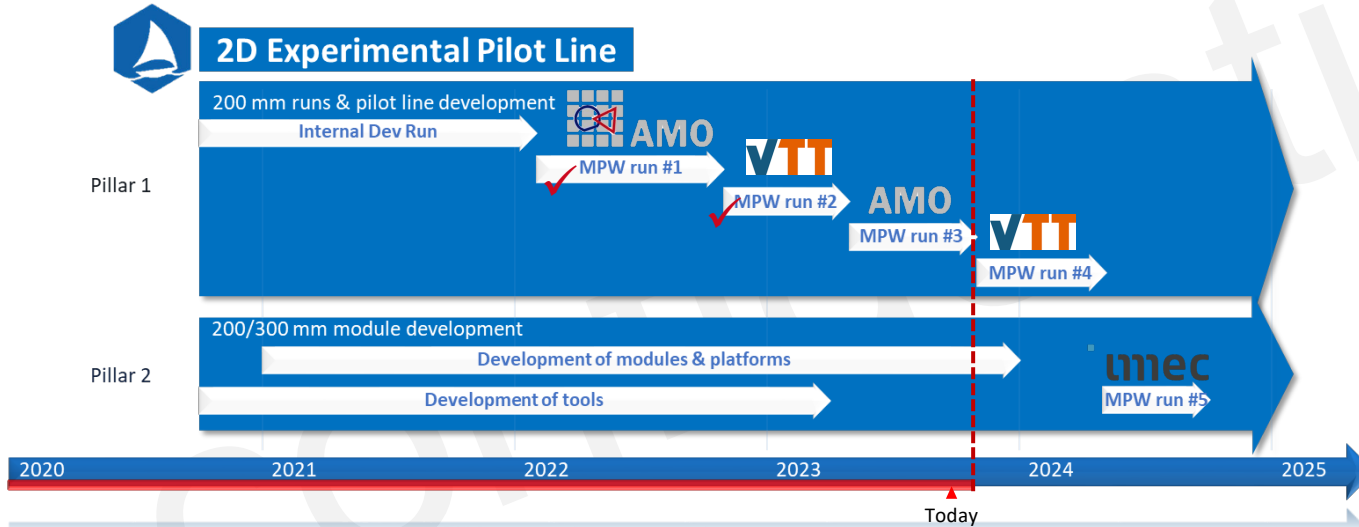
Nokia

ELMOS

2D Materials for Energy Harvesting

European 2D Experimental Pilot Line

2D EPL Project Timeline (MPW runs)



Run 1
AMO **DELIVERED**
 Graphene Sensors
 Dec 2023

Run 2
VTT **DELIVERED**
 Graphene Sensors
 June 2023

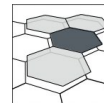
Run 3
AMO **Execution**
 Electronic Devices incl.
 Graphene Sensors
 Oct 2023

Run 4
VTT **Design**
 Graphene Sensors devices on
 CMOS wafers
 June 2024

Run 5
imec
 TMDC based transistors
 Oct 2024

+ additional runs

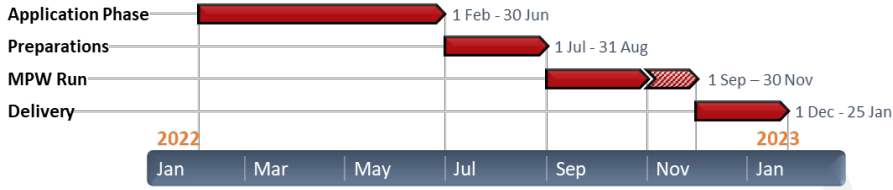
Development of tools, modules and platforms in parallel with the offer of MPW runs.



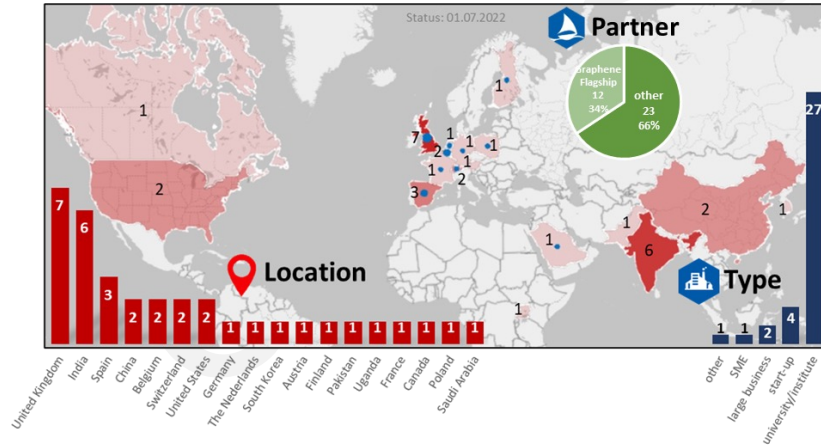
2D Materials for Energy Harvesting

The 2D Experimental Pilot Line

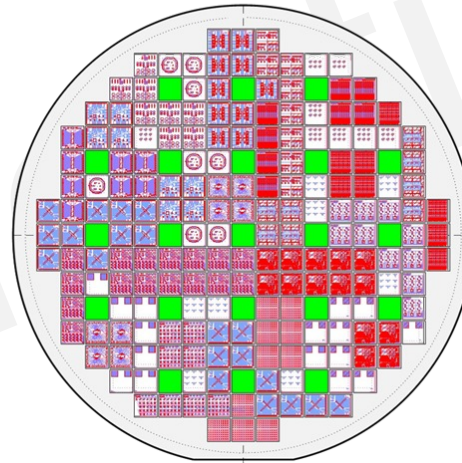
Multi-Project Wafer Run #1



Overall applications

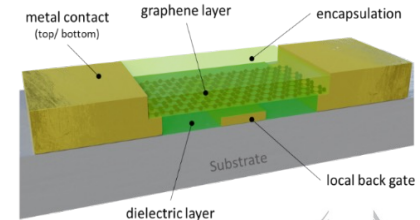


35 applications => 14 participating customers



Mask with customer dies distributed over 8" wafer; 21 different designs, 108 order dies

1. Back Gate & Contacts
2. Dielectric
3. Graphene Transfer
4. Contacts & Encapsulation
5. Opening of encapsulation



2D Materials for Energy Harvesting



This project has received funding from the European Union's Horizon 2020 research and innovation programme under grant agreement No 101006963 (GreEnergy).



More information is available at www.greenergy-project.eu

